

FEB 28 2003

PATENT & TRADEMARK OFFICE

Atty. Docket No. 8020-1002-1

PATENTS

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Yoshiaki HISAMUNE et al.

Confirmation No. 3150

Serial No. 10/083,611

GROUP 2812

Filed February 27, 2002

Examiner Richard A. Booth

METHOD OF MANUFACTURING SEMICONDUCTOR  
DEVICE, NONVOLATILE SEMICONDUCTOR MEMORY  
DEVICE AND METHOD OF MANUFACTURING THE  
SAME

AMENDMENT

Commissioner for Patents

Washington, D.C. 20231

Sir:

Responsive to the Official Action of December 3, 2002,  
please amend the above-identified application as follows:

IN THE SPECIFICATION:

Page 23, replace the paragraph beginning on line 4 as  
follows:

*A* [Then, as shown in Figs. 7A, 7B and 7C, an N-type  
impurity, for example such as arsenic ions is injected into the  
P-type semiconductor substrate 1 in a self-align manner with the  
use of the lower floating gate 4 and the device isolation  
shielding electrode 9 as masks.]

IN THE CLAIMS:

Amend claim 1 as follows:

*A* 1. (amended) In a method of manufacturing a

*A2*

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